





#### **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features**

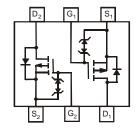
- Dual P-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage V<sub>GS(th)</sub> < 1V</li>
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.015 grams (approximate)







Top View Internal Schematic

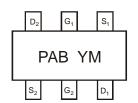
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2004DMK-7	SOT26	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



PAB = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

#### Date Code Key

Year	2007	2008	2009	2010	201	1 20	12	2013	2014	2015	2016	2017
Code	U	V	W	X	Y		Z	Α	В	С	D	E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	J Sep	Oct	Nov	Dec



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	±8	V
Drain Current (Note 5)	I <sub>D</sub>	-550	mA
Pulsed Drain Current	I <sub>DM</sub>	-1.9	А

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	$P_{D}$	500	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	250	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

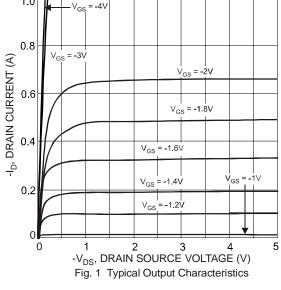
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

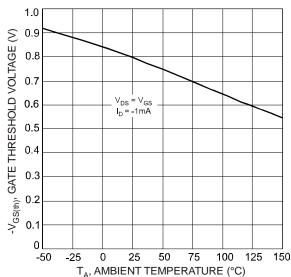
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)			. , , ,	max	O	reet containen	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	
Zero Gate Voltage Drain Current	IDSS		_	-1.0	μΑ	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±1.0	μА	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			0.7	0.9		$V_{GS} = -4.5V, I_D = -430mA$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	1.1	1.4	Ω	$V_{GS} = -2.5V, I_D = -300mA$	
			1.7	2.0		$V_{GS} = -1.8V, I_D = -150mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	200	_	_	mS	$V_{DS} = 10V, I_{D} = -0.2A$	
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	-0.5	_	-1.2	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>iss</sub>	_	_	175	pF		
Output Capacitance	Coss		_	30	pF	$V_{DS} = -16V, V_{GS} = 0V$	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	20	pF	-f = 1.0MHz	

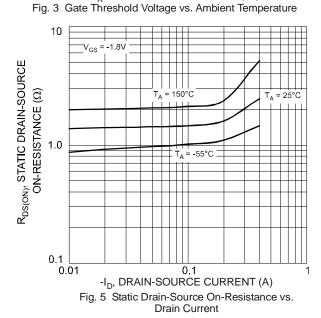
Notes:

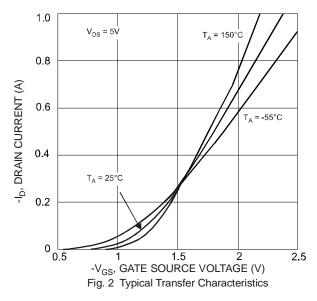
- 5. Device mounted on FR-4 PCB.
- 6. Short duration pulse test used to minimize self-heating effect.

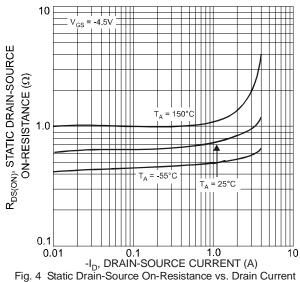


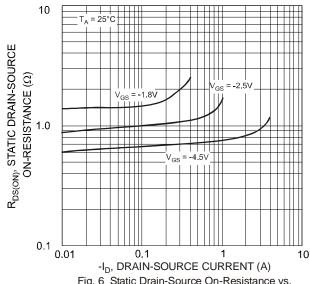














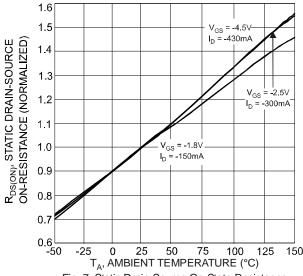


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

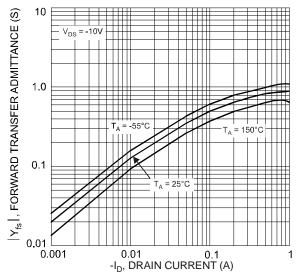


Fig. 9 Forward Transfer Admittance vs. Drain Current

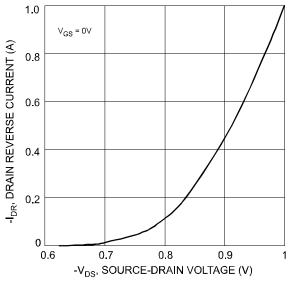
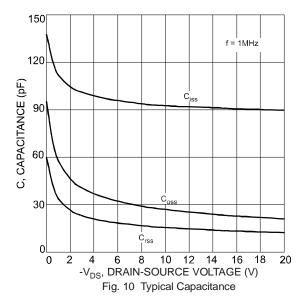
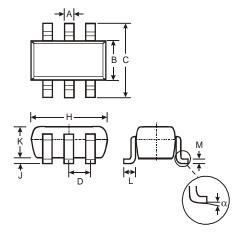


Fig. 8 Drain Reverse Current vs. Source-Drain Voltage



# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

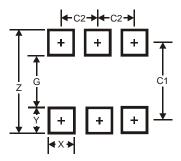


	SOT26						
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	_	_	0.95				
Н	2.90	3.10	3.00				
7	0.013	0.10	0.05				
K	1.00	1.30	1.10				
L	0.35	0.55	0.40				
M	0.10	0.20	0.15				
α	0°	8°	_				
All D	All Dimensions in mm						



## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

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